

## 1. General description

Planar passivated very sensitive gate four quadrant triac in a SOT54 plastic package intended to be interfaced directly to microcontrollers, logic integrated circuits and other low power gate trigger circuits.

## 2. Features and benefits

- Direct interfacing to logic level ICs
- Direct interfacing to low power gate drivers and microcontrollers
- High blocking voltage capability
- Planar passivated for voltage ruggedness and reliability
- Triggering in all four quadrants
- Very sensitive gate

## 3. Applications

- General purpose low power phase control
- General purpose low power switching
- Solid-state relay

## 4. Quick reference data

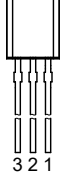

Table 1. Quick reference data

| Symbol                        | Parameter                            | Conditions  | Min | Typ | Max | Unit |
|-------------------------------|--------------------------------------|---|-----|-----|-----|------|
| $V_{DRM}$                     | repetitive peak off-state voltage    |   | -   | -   | 600 | V    |
| $I_{T(RMS)}$                  | RMS on-state current                 | full sine wave; $T_{lead} \leq 50\text{ °C}$ ; <a href="#">Fig. 1</a> ; <a href="#">Fig. 2</a> ; <a href="#">Fig. 3</a> | -   | -   | 0.6 | A    |
| $I_{TSM}$                     | non-repetitive peak on-state current | full sine wave; $T_{j(init)} = 25\text{ °C}$ ; $t_p = 20\text{ ms}$ ; <a href="#">Fig. 4</a> ; <a href="#">Fig. 5</a>   | -   | -   | 8   | A    |
|                               |                                      | full sine wave; $T_{j(init)} = 25\text{ °C}$ ; $t_p = 16.7\text{ ms}$   | -   | -   | 8.8 | A    |
| $T_j$                         | junction temperature                 |   | -   | -   | 125 | °C   |
| <b>Static characteristics</b> |                                      |   |     |     |     |      |
| $I_{GT}$                      | gate trigger current                 | $V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; T2+ G+; $T_j = 25\text{ °C}$ ; <a href="#">Fig. 7</a>                      | -   | 1   | 5   | mA   |
|                               |                                      | $V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; T2+ G-; $T_j = 25\text{ °C}$ ; <a href="#">Fig. 7</a>                      | -   | 2   | 5   | mA   |
|                               |                                      | $V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; T2- G-; $T_j = 25\text{ °C}$ ; <a href="#">Fig. 7</a>                      | -   | 2   | 5   | mA   |

| Symbol                         | Parameter                             | Conditions   | Min | Typ | Max | Unit       |
|--------------------------------|---------------------------------------|--|-----|-----|-----|------------|
|                                |                                       | $V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; T2- G+;<br>$T_j = 25\text{ °C}$ ; <a href="#">Fig. 7</a>  | -   | 4   | 7   | mA         |
| $I_H$                          | holding current                       | $V_D = 12\text{ V}$ ; $T_j = 25\text{ °C}$ ; <a href="#">Fig. 9</a>  | -   | 1   | 10  | mA         |
| $V_T$                          | on-state voltage                      | $I_T = 0.85\text{ A}$ ; $T_j = 25\text{ °C}$ ; <a href="#">Fig. 10</a>   | -   | 1.4 | 1.9 | V          |
| <b>Dynamic characteristics</b> |                                       |  |     |     |     |            |
| $dV_D/dt$                      | rate of rise of off-state voltage     | $V_{DM} = 402\text{ V}$ ; $T_j = 110\text{ °C}$ ; ( $V_{DM} = 67\%$ of $V_{DRM}$ ); exponential waveform; gate open circuit; <a href="#">Fig. 12</a> | 30  | 45  | -   | V/ $\mu$ s |
| $dV_{com}/dt$                  | rate of change of commutating voltage | $V_D = 600\text{ V}$ ; $T_j = 50\text{ °C}$ ; $dI_{com}/dt = 0.3\text{ A/ms}$ ; $I_T = 0.84\text{ A}$ ; gate open circuit                            | -   | 5   | -   | V/ $\mu$ s |

## 5. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description     | Simplified outline  | Graphic symbol   |
|-----|--------|-----------------|---|--|
| 1   | T2     | main terminal 2 |  <p>TO-92 (SOT54)</p> |  <p>sym051</p> |
| 2   | G      | gate            |   |  |
| 3   | T1     | main terminal 1 |   |  |

## 6. Ordering information

Table 3. Ordering information

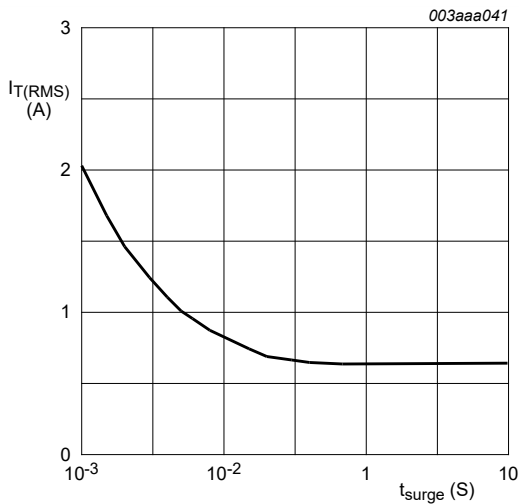
| Type number | Package |   |         |
|-------------|---------|---|---------|
|             | Name    | Description   | Version |
| MAC97A8     | TO-92   | plastic single-ended leaded (through hole) package; 3 leads | SOT54   |

## 7. Limiting values

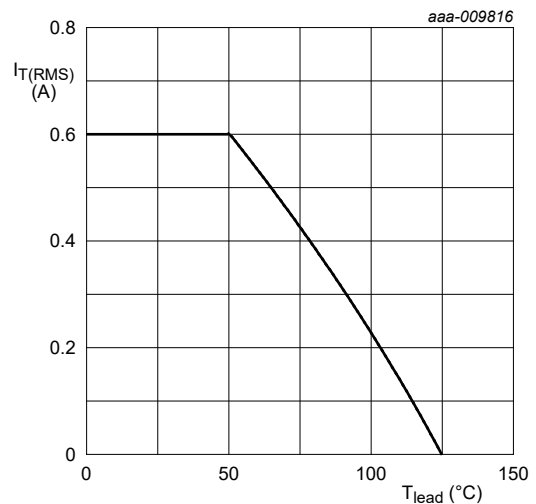
**Table 4. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol       | Parameter                            | Conditions  | Min | Max  | Unit             |
|--------------|--------------------------------------|---|-----|------|------------------|
| $V_{DRM}$    | repetitive peak off-state voltage    |   | -   | 600  | V                |
| $I_{T(RMS)}$ | RMS on-state current                 | full sine wave; $T_{lead} \leq 50\text{ °C}$ ; <a href="#">Fig. 1</a> ; <a href="#">Fig. 2</a> ; <a href="#">Fig. 3</a> | -   | 0.6  | A                |
| $I_{TSM}$    | non-repetitive peak on-state current | full sine wave; $T_{j(init)} = 25\text{ °C}$ ; $t_p = 20\text{ ms}$ ; <a href="#">Fig. 4</a> ; <a href="#">Fig. 5</a>   | -   | 8    | A                |
|              |                                      | full sine wave; $T_{j(init)} = 25\text{ °C}$ ; $t_p = 16.7\text{ ms}$   | -   | 8.8  | A                |
| $I^2t$       | $I^2t$ for fusing                    | $t_p = 10\text{ ms}$ ; SIN  | -   | 0.32 | A <sup>2</sup> s |
| $di_T/dt$    | rate of rise of on-state current     | $I_G = 20\text{ mA}$ ; T2+ G+   | -   | 50   | A/ $\mu$ s       |
|              |                                      | $I_G = 20\text{ mA}$ ; T2+ G-   | -   | 50   | A/ $\mu$ s       |
|              |                                      | $I_G = 20\text{ mA}$ ; T2- G-   | -   | 50   | A/ $\mu$ s       |
|              |                                      | $I_G = 20\text{ mA}$ ; T2- G+   | -   | 10   | A/ $\mu$ s       |
| $I_{GM}$     | peak gate current                    |   | -   | 1    | A                |
| $P_{GM}$     | peak gate power                      |   | -   | 5    | W                |
| $P_{G(AV)}$  | average gate power                   | over any 20 ms period   | -   | 0.1  | W                |
| $T_{stg}$    | storage temperature                  |   | -40 | 150  | °C               |
| $T_j$        | junction temperature                 |   | -   | 125  | °C               |



**Fig. 1. RMS on-state current as a function of surge duration; maximum values**



**Fig. 2. RMS on-state current as a function of lead temperature; maximum values**

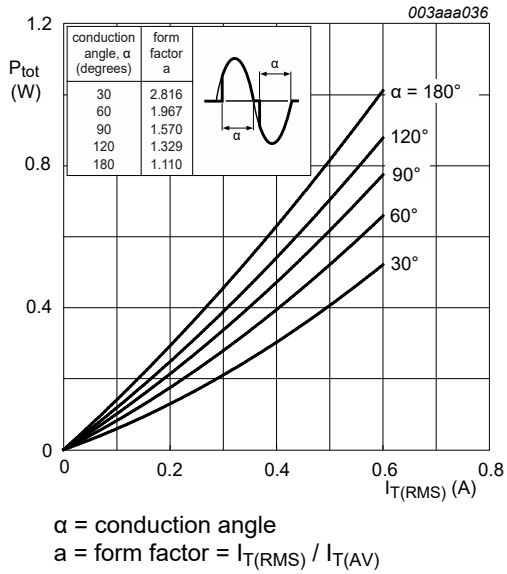


Fig. 3. Total power dissipation as a function of RMS on-state current; maximum values

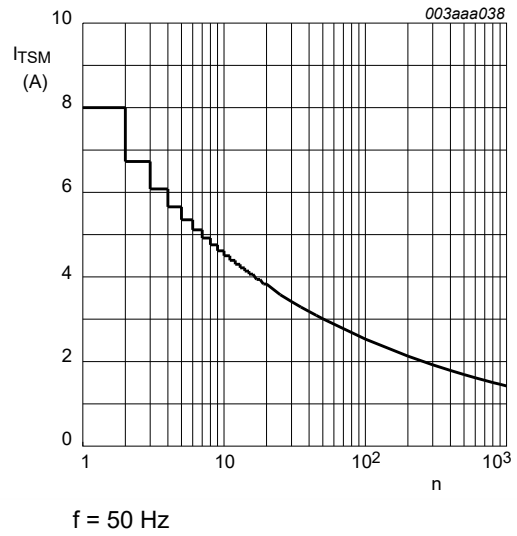


Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values

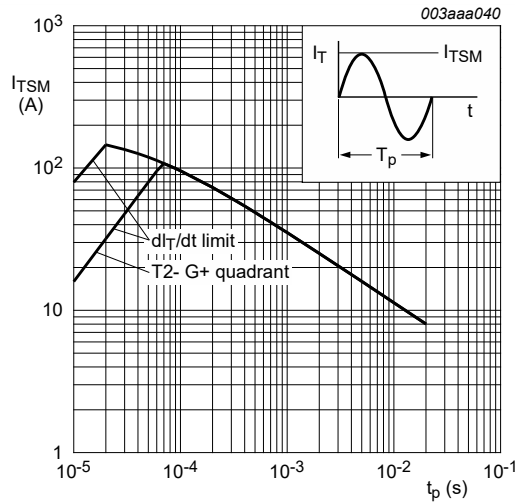


Fig. 5. Non-repetitive peak on-state current as a function of pulse width; maximum values

## 8. Thermal characteristics

Table 5. Thermal characteristics

| Symbol                  | Parameter  | Conditions  | Min | Typ | Max | Unit |
|-------------------------|--|---|-----|-----|-----|------|
| R <sub>th(j-lead)</sub> | thermal resistance from junction to lead             | full cycle; <a href="#">Fig. 6</a>                | -   | -   | 60  | K/W  |
|                         |  | half cycle  | -   | -   | 80  | K/W  |
| R <sub>th(j-a)</sub>    | thermal resistance from junction to ambient free air | printed circuit board mounted: lead length = 4 mm | -   | 150 | -   | K/W  |

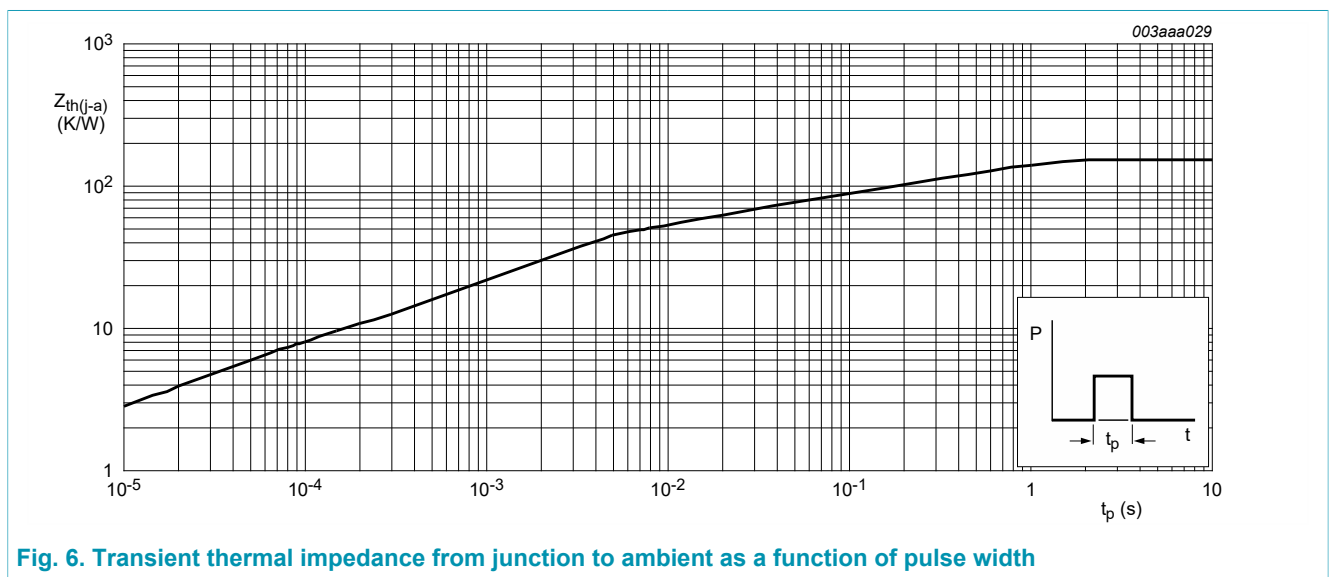


Fig. 6. Transient thermal impedance from junction to ambient as a function of pulse width

## 9. Characteristics

Table 6. Characteristics

| Symbol                         | Parameter                             | Conditions   | Min | Typ | Max | Unit                   |
|--------------------------------|---------------------------------------|--|-----|-----|-----|------------------------|
| <b>Static characteristics</b>  |                                       |  |     |     |     |                        |
| $I_{GT}$                       | gate trigger current                  | $V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; T2+ G+;<br>$T_j = 25\text{ °C}$ ; <a href="#">Fig. 7</a>  | -   | 1   | 5   | mA                     |
|                                |                                       | $V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; T2+ G-;<br>$T_j = 25\text{ °C}$ ; <a href="#">Fig. 7</a>  | -   | 2   | 5   | mA                     |
|                                |                                       | $V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; T2- G-;<br>$T_j = 25\text{ °C}$ ; <a href="#">Fig. 7</a>  | -   | 2   | 5   | mA                     |
|                                |                                       | $V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; T2- G+;<br>$T_j = 25\text{ °C}$ ; <a href="#">Fig. 7</a>  | -   | 4   | 7   | mA                     |
| $I_L$                          | latching current                      | $V_D = 12\text{ V}$ ; $I_G = 0.1\text{ A}$ ; T2+ G+;<br>$T_j = 25\text{ °C}$ ; <a href="#">Fig. 8</a>  | -   | 1   | 10  | mA                     |
|                                |                                       | $V_D = 12\text{ V}$ ; $I_G = 0.1\text{ A}$ ; T2+ G-;<br>$T_j = 25\text{ °C}$ ; <a href="#">Fig. 8</a>  | -   | 5   | 10  | mA                     |
|                                |                                       | $V_D = 12\text{ V}$ ; $I_G = 0.1\text{ A}$ ; T2- G-;<br>$T_j = 25\text{ °C}$ ; <a href="#">Fig. 8</a>  | -   | 1   | 10  | mA                     |
|                                |                                       | $V_D = 12\text{ V}$ ; $I_G = 0.1\text{ A}$ ; T2- G+;<br>$T_j = 25\text{ °C}$ ; <a href="#">Fig. 8</a>  | -   | 2   | 10  | mA                     |
| $I_H$                          | holding current                       | $V_D = 12\text{ V}$ ; $T_j = 25\text{ °C}$ ; <a href="#">Fig. 9</a>  | -   | 1   | 10  | mA                     |
| $V_T$                          | on-state voltage                      | $I_T = 0.85\text{ A}$ ; $T_j = 25\text{ °C}$ ; <a href="#">Fig. 10</a>   | -   | 1.4 | 1.9 | V                      |
| $V_{GT}$                       | gate trigger voltage                  | $V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; $T_j = 25\text{ °C}$ ;<br><a href="#">Fig. 11</a>   | -   | 0.9 | 1.5 | V                      |
|                                |                                       | $V_D = 400\text{ V}$ ; $I_T = 0.1\text{ A}$ ; $T_j = 110\text{ °C}$ ;<br><a href="#">Fig. 11</a>   | 0.1 | 0.7 | -   | V                      |
| $I_D$                          | off-state current                     | $V_D = 600\text{ V}$ ; $T_j = 110\text{ °C}$   | -   | 3   | 100 | $\mu\text{A}$          |
| <b>Dynamic characteristics</b> |                                       |  |     |     |     |                        |
| $dV_D/dt$                      | rate of rise of off-state voltage     | $V_{DM} = 402\text{ V}$ ; $T_j = 110\text{ °C}$ ; ( $V_{DM} = 67\%$ of $V_{DRM}$ ); exponential waveform; gate open circuit; <a href="#">Fig. 12</a> | 30  | 45  | -   | $\text{V}/\mu\text{s}$ |
| $dV_{com}/dt$                  | rate of change of commutating voltage | $V_D = 600\text{ V}$ ; $T_j = 50\text{ °C}$ ; $dI_{com}/dt = 0.3\text{ A/ms}$ ; $I_T = 0.84\text{ A}$ ; gate open circuit                            | -   | 5   | -   | $\text{V}/\mu\text{s}$ |
| $t_{gt}$                       | gate-controlled turn-on time          | $I_{TM} = 1\text{ A}$ ; $V_D = 600\text{ V}$ ; $I_G = 25\text{ mA}$ ; $dI_G/dt = 5\text{ A}/\mu\text{s}$   | -   | 2   | -   | $\mu\text{s}$          |

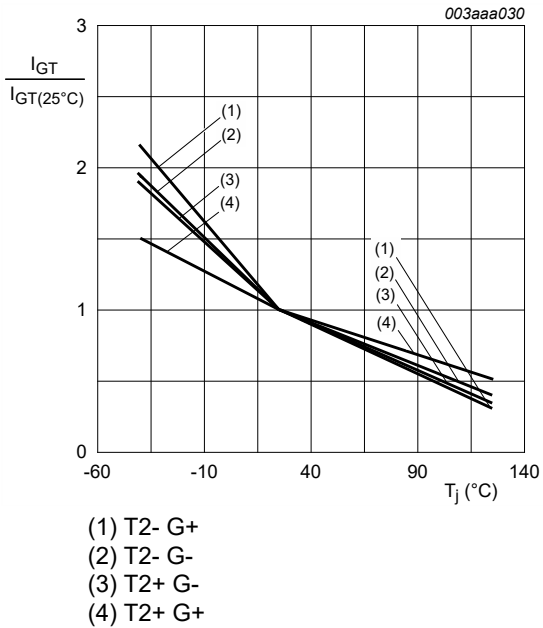


Fig. 7. Normalized gate trigger current as a function of junction temperature

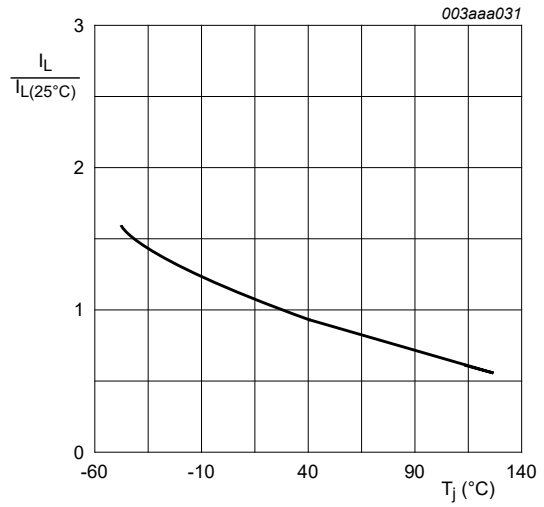


Fig. 8. Normalized latching current as a function of junction temperature

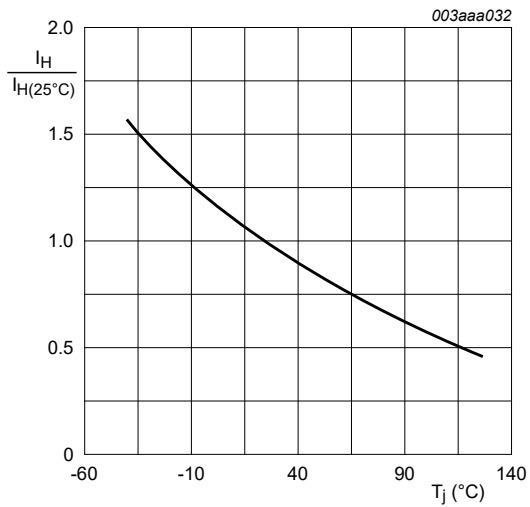
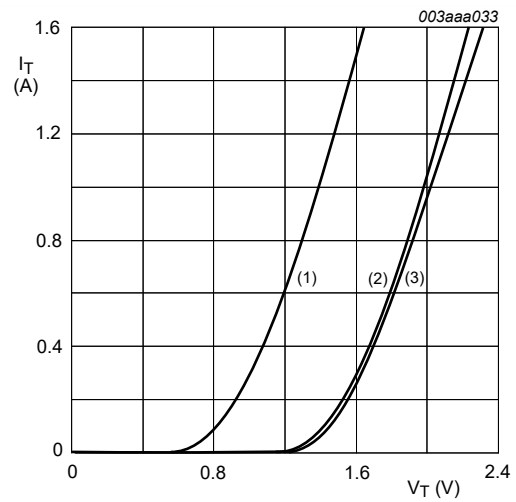


Fig. 9. Normalized holding current as a function of junction temperature



$V_o = 1.45\text{ V}; R_s = 0.1875\ \Omega$

- (1)  $T_j = 125^\circ\text{C}$ ; typical values
- (2)  $T_j = 125^\circ\text{C}$ ; maximum values
- (3)  $T_j = 25^\circ\text{C}$ ; maximum values

Fig. 10. On-state current as a function of on-state voltage

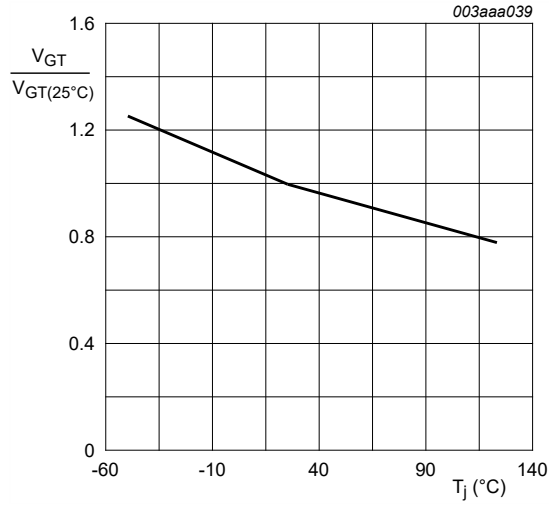


Fig. 11. Normalized gate trigger voltage as a function of junction temperature

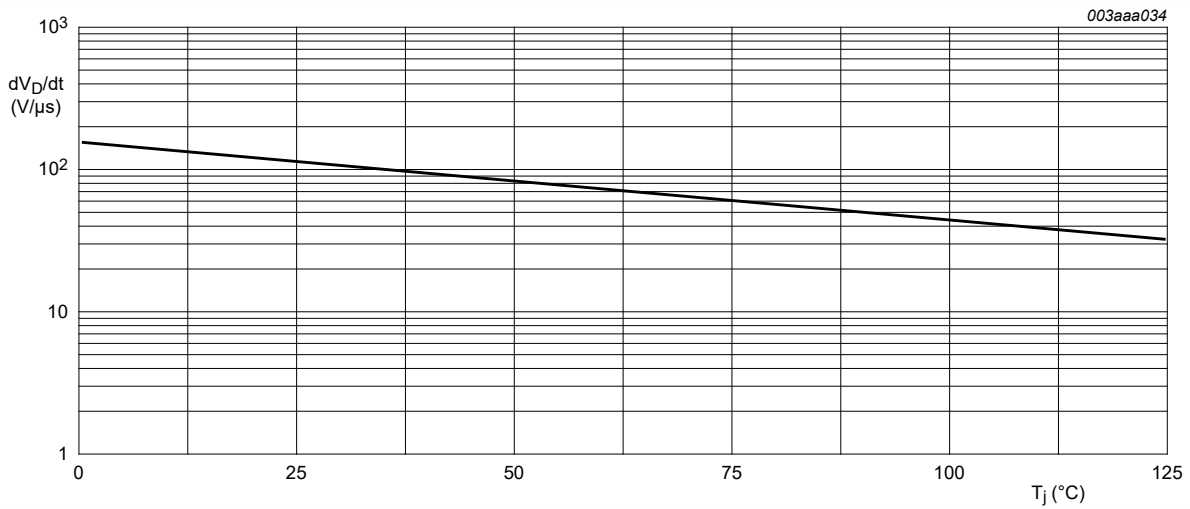


Fig. 12. Critical rate of rise of off-state voltage as a function of junction temperature; typical values



### 10. Package outline

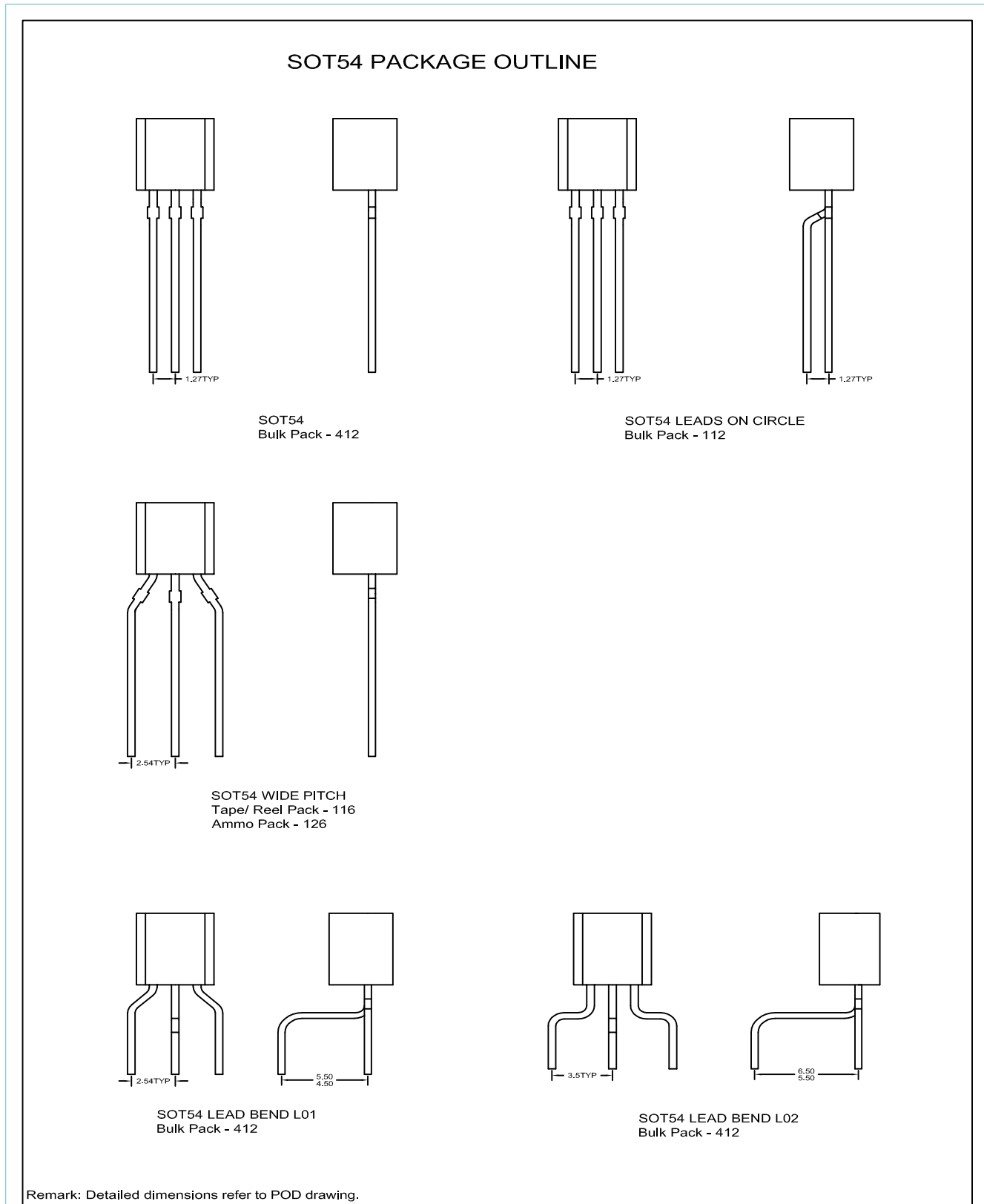


Fig. 13. Package outline TO-92 (SOT54)

# 11. Legal information

## Data sheet status

| Document status [1][2]         | Product status [3] | Definition  |
|--------------------------------|--------------------|---|
| Objective [short] data sheet   | Development        | This document contains data from the objective specification for product development. |
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- [1] Please consult the most recently issued document before initiating or completing a design.
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Date of release: 15 September 2018

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